

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
Stylesheet Version v1.2

Assignment ID: PATI84357

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
NEXGEN POWER SYSTEMS, INC.	03/08/2024
RECEIVING PARTY DATA	
Company Name:	SEMICONDUCTOR COMPONENTS INDUSTRIES, LLC
Street Address:	5701 N. Pima Road
City:	Scottsdale
State/Country:	ARIZONA
Postal Code:	85250
PROPERTY NUMBERS Total: 121	
Property Type	Number
Application Number:	13301165
Application Number:	14558393
Application Number:	13326192
Application Number:	14657949
Application Number:	13198655
Application Number:	13198659
Application Number:	14604600
Application Number:	13198661
Application Number:	14611041
Application Number:	13198666
Application Number:	13225345
Application Number:	13289219
Application Number:	13935345
Application Number:	14574265
Application Number:	13270606
Application Number:	13240877
Application Number:	14498916
Application Number:	13270625
Application Number:	14299773
Application Number:	13315705

Property Type	Number
Application Number:	13300009
Application Number:	14479634
Application Number:	13300028
Application Number:	13299227
Application Number:	13932290
Application Number:	13335572
Application Number:	14489761
Application Number:	13335329
Application Number:	14454524
Application Number:	14834306
Application Number:	13307108
Application Number:	14061741
Application Number:	13270641
Application Number:	14594778
Application Number:	13299254
Application Number:	14264998
Application Number:	13335355
Application Number:	13315720
Application Number:	14192662
Application Number:	14606822
Application Number:	13334742
Application Number:	14220564
Application Number:	13465812
Application Number:	14815780
Application Number:	13334514
Application Number:	14471374
Application Number:	13335383
Application Number:	13529822
Application Number:	14302270
Application Number:	13468325
Application Number:	13468332
Application Number:	13675694
Application Number:	14604606
Application Number:	13552365
Application Number:	14815751
Application Number:	13572408
Application Number:	13585121
Application Number:	14602125

Property Type	Number
Application Number:	13611467
Application Number:	13692717
Application Number:	14803552
Application Number:	13571743
Application Number:	15681823
Application Number:	13675916
Application Number:	13675826
Application Number:	13730619
Application Number:	13735912
Application Number:	13721542
Application Number:	14517564
Application Number:	14077039
Application Number:	13866286
Application Number:	14853930
Application Number:	13901546
Application Number:	14045708
Application Number:	14071032
Application Number:	15697161
Application Number:	16423414
Application Number:	16789781
Application Number:	14095759
Application Number:	14083217
Application Number:	15697170
Application Number:	29501217
Application Number:	29525732
Application Number:	16929926
Application Number:	17719221
Application Number:	18213781
Application Number:	17131568
Application Number:	18119717
Application Number:	17135436
Application Number:	18587327
Application Number:	16929896
Application Number:	17707833
Application Number:	17350237
Application Number:	18085985
Application Number:	18371956
Application Number:	17356042

Property Type	Number
Application Number:	17211562
Application Number:	18213707
Application Number:	17369600
Application Number:	17373627
Application Number:	17524030
Application Number:	17524064
Application Number:	17524067
Application Number:	17498426
Application Number:	17524117
Application Number:	18233255
Application Number:	17524126
Application Number:	17524136
Application Number:	18371332
Application Number:	17667432
Application Number:	17584215
Application Number:	17707835
Application Number:	17707839
Application Number:	18108457
Application Number:	18137329
Application Number:	18097693
Application Number:	18097683
Application Number:	18097994
Application Number:	18137314
Application Number:	18137093
Application Number:	18137075

CORRESPONDENCE DATA

Fax Number:

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Phone: 6022443574

Email: patents@onsemi.com

Correspondent Name: Michelle Smojver

Address Line 1: 5701 N. Pima Road

Address Line 4: Scottsdale, ARIZONA 85250

ATTORNEY DOCKET NUMBER:	NexGen-SCI
NAME OF SUBMITTER:	Michelle Smojver
SIGNATURE:	Michelle Smojver
DATE SIGNED:	03/11/2024

Total Attachments: 8

source=Nexgen-SCI_IP Assignment_2024.03.11#page1.tif

source=Nexgen-SCI_IP Assignment_2024.03.11#page2.tif

source=Nexgen-SCI_IP Assignment_2024.03.11#page3.tif

source=Nexgen-SCI_IP Assignment_2024.03.11#page4.tif

source=Nexgen-SCI_IP Assignment_2024.03.11#page5.tif

source=Nexgen-SCI_IP Assignment_2024.03.11#page6.tif

source=Nexgen-SCI_IP Assignment_2024.03.11#page7.tif

source=Nexgen-SCI_IP Assignment_2024.03.11#page8.tif

INTELLECTUAL PROPERTY ASSIGNMENT AGREEMENT

This Intellectual Property Assignment Agreement (the "Assignment") is hereby entered into on March 8, 2024 (the "Effective Date"), by, between, and among Nexgen (assignment for the benefit of creditors), LLC, a California limited liability company, in its sole and limited capacity as assignee for the benefit of creditors of Nexgen Power Systems, Inc. ("Assignor"), and Semiconductor Components Industries, LLC ("Assignee").

1. Assignor desires to transfer and assign to Assignee, and Assignee desires to accept the transfer and assignment of all of Assignor's right, title and interest in, to and under, all of the following (hereafter collectively referred to as "Intellectual Property"):

(i) the entire worldwide right, title and interest of Assignor in and to each and all patents in the United States and in all foreign countries including, without limitation corresponding Patent Cooperation Treaty patent applications and corresponding National patent applications and all inventions, improvements and discoveries disclosed in said patents, patent applications, patent drafts, and invention disclosures, including but not limited to those set forth in **Schedule A** hereto, and in and to all substitutions, divisions, continuations, continuations-in-part, reexaminations, extensions, renewals and reissues (as applicable) thereof, including without limitation of generality, all rights of priority resulting from the filing of patent applications relating to any of the foregoing as well as any and all choses in action and any and all claims and demands, both at law and in equity, that Assignor has or may have for damages or profits accrued or to accrue on account of the infringement of any of said patents, patent applications, inventions, improvements and discoveries (or any provisional rights therein), the same to be held and enjoyed by Assignee, its successors and assigns, as fully and entirely as the same would have been held and enjoyed by Assignor if the assignment set forth in this Assignment had not been made;

(ii) the full and complete right to file patent applications in the name of Assignee, its successors, and assigns, or anyone it may properly designate including the Assignor, on the aforesaid inventions, improvements, discoveries and applications in all countries of the world;

(iii) the entire right, title and interest of Assignor in and to any patent which may issue thereon in the United States or in any country, and any renewals, revivals, reissues, reexaminations and extensions thereof, and any patents of confirmation, registration and importation of the same;

(iv) any and all trademark and servicemark rights throughout the world, including any and all applications, registrations, and common law marks, whether registered or not, together with the goodwill of the business associated with and symbolized by same, held by Assignor and any and all domain names, including but not limited to those set forth on **Schedule B** hereto, together with all common law rights therein, and the right of Assignor to sue for and recover damages or profits arising out of past, present, or future

infringement of any and all of said rights as fully and entirely as the same would have been held and enjoyed by Assignor had this Assignment not been made;

(v) any and all copyrights throughout the world, including any and all applications, registrations, and like protections, whether registered or not, whether published or unpublished, together with all common law rights therein, and the right of Assignor to sue for and recover damages or profits arising out of past, present, or future infringement of any and all of said rights as fully and entirely as the same would have been held and enjoyed by Assignor had this Assignment not been made;

(vi) any and all trade secret rights, including rights Assignor may have under the laws governing confidential information or rights in law to prevent the unauthorized use or disclosure of such information.

2. Assignor, for good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, does hereby sell, convey, transfer and assign to Assignee, and Assignee hereby accepts the sale, conveyance, transfer and assignment of all right, title and interest of Assignor in, to and under the Intellectual Property, including all worldwide right, title and interest of Assignor in, to and under the Intellectual Property, together with the right of Assignor to claim priority in all countries in accordance with international law, any and all rights of Assignor corresponding to said Intellectual Property in countries throughout the world, and all of Assignor's rights to sue for past, present or future infringement of said Intellectual Property worldwide together with all claims for damages by reason of past, present or future infringement of said Intellectual Property, and the right to sue for and collect the same for Assignee's own use and enjoyment, all to be held and enjoyed by said Assignee, its successors and assigns, as fully and entirely as the same would have been held and enjoyed by Assignor had this Assignment not been made. Assignor hereby authorizes and requests the United States Patent and Trademarks Office to issue said Patents and Trademarks in accordance with this Assignment.

3. Assignor represents and warrants that Assignor has made no other agreements establishing any other encumbrances, liens, security interests, or third-party interests on or to the Intellectual Property, and that Assignor has full and complete right, title, and authority to make this Assignment.

4. This Assignment may be executed in multiple counterparts, each of which shall be deemed an original hereof, and all of which shall constitute a single agreement effective as of the date hereof. Any delivery of an executed counterpart of this Assignment by facsimile or electronic mail shall be as effective as delivery of a manually executed counterpart of this Assignment.

5. This Assignment shall be binding upon and shall inure to the benefit of the parties and their respective successors and assigns.

6. This Assignment shall be governed by and construed in accordance with federal law, to the extent applicable, and, where state law is implicated, the internal laws of the State of California, without giving effect to any principles of conflicts of law.

IN WITNESS WHEREOF, Assignor and Assignee executed and delivered this Assignment by their duly authorized representatives as of the Effective Date.

Nexgen (assignment for the benefit of creditors), LLC, solely as Assignee for the benefit of creditors of Nexgen Power Systems, Inc. (Assignor)

By: Michael Maidy

Name: Michael Maidy

Title: Manager for Nexgen (assignment for the benefit of creditors), LLC
in its sole and limited capacity as Assignee for the benefit of the
creditors of Nexgen Power Systems, Inc.

[to be completed by notary public]

On this 7 day of March, before me, Carissa Kozacek, the undersigned Notary Public, personally appeared Michael Maidy on behalf of Nexgen (assignment for the benefit of creditors), LLC, in its sole and limited capacity as assignee for the benefit of creditors of Nexgen Power Systems, Inc., personally known to me (or proved to me on the basis of satisfactory evidence) to be the person whose name is subscribed to the within instrument, and acknowledged to me that the same was signed in their authorized capacity and that by this signature Nexgen (assignment for the benefit of creditors), LLC executed the instrument.

In witness whereof, I hereunto set my hand and official seal:

Carissa Kozacek
(notary signature)

Semiconductor Components Industries, LLC (Assignee)

By: Hassane El-Khoury
DocuSigned by:
84AE478E4C96444...

Name: Hassane El-Khoury

Title: President and CEO

SCHEDULE A

Patents

[See attached.]

EXHIBIT A
Nexgen ABC Patents

#	FILE NO.	IP FAMILY NO.	TITLE	COUNTRY	APPLN. NO.	FILING DATE	PUB. NO.	PUB. DATE	PATENT NO.	ISSUE DATE	STATUS	INVENTORS
1	102584-0826397	000400US	EDGE TERMINATION BY ION IMPLANTATION IN GAN	USA	13/301,165	Nov 21, 2011	US-2013-0126888-A1	May 23, 2013	8,927,999	Jan 6, 2015	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David Bour, Richard J. Brown, Thomas R. Prunty
2	102584-0926339	000410US	EDGE TERMINATION BY ION IMPLANTATION IN GALLIUM NITRIDE	USA	14/558,393	Dec 2, 2014	US-2015-0200097-A1	Jul 16, 2015	9,330,918	May 3, 2016	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
3	102584-0824389	000500US	INGAN OHMIC SOURCE CONTACTS FOR VERTICAL POWER DEVICES	USA	13/326,192	Dec 14, 2011	US-2013-0153917-A1	Jun 20, 2013	9,006,800	Apr 14, 2015	Issued	Linda Romano, Andrew Edwards, Dave P. Bour, Isik C. Kizilyalli
4	102584-0938799	000510US	INGAN OHMIC SOURCE CONTACTS FOR VERTICAL POWER DEVICES	USA	14/657,949	Mar 13, 2015	US-2015-0255582-A1	Sep 10, 2015	9,508,838	Nov 29, 2016	Issued	Linda Romano, Andrew Edwards, Dave P. Bour, Isik C. Kizilyalli
5	102584-0808244	000600US	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REGROWN GATE	USA	13/198,655	Aug 4, 2011	US-2013-0032811-A1	Feb 7, 2013	9,184,305	Nov 10, 2015	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
6	102584-0808236	000700US	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REGROWN CHANNEL	USA	13/198,659	Aug 4, 2011	US-2013-0032812-A1	Feb 7, 2013	8,969,912	Mar 3, 2015	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
7	102584-0929267	000710US	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REGROWN CHANNEL	USA	14/604,600	Jan 23, 2015	US-2015-0132899-A1	May 14, 2015	9,324,844	Apr 26, 2016	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
8	102584-0808237	000800US	METHOD AND SYSTEM FOR DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	USA	13/198,661	Aug 4, 2011	US-2013-0032813-A1	Feb 7, 2013	8,946,788	Feb 3, 2015	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
9	102584-0933699	000810US	METHOD AND SYSTEM FOR DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	USA	14/611,041	Jan 30, 2015	US-2015-0153372-A1	Jun 4, 2015	9,287,389	Mar 15, 2016	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
10	102584-0808239	000900US	METHOD AND SYSTEM FOR FORMATION OF P-N JUNCTIONS IN GALLIUM NITRIDE BASED ELECTRONICS	USA	13/198,666	Aug 4, 2011	US-2013-0032814-A1	Feb 7, 2013	9,136,116	Sep 15, 2015	Issued	David P. Bour, Thomas R. Prunty, Linda Romano, Andrew P. Edwards, Isik C. Kizilyalli, Hui Nie, Richard J. Brown, Mahdhan Raj
11	102584-0808243	001000US	METHOD AND SYSTEM FOR LOCAL CONTROL OF DEFECT DENSITY IN GALLIUM NITRIDE BASED ELECTRONICS	USA	13/225,345	Sep 2, 2011	US-2013-0056743-A1	Mar 7, 2013	9,093,395	Jul 28, 2015	Issued	David P. Bour, Linda Romano, Thomas R. Prunty, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown
12	102584-0813851	001100US	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	USA	13/289,219	Nov 4, 2011	US-2013-0112985-A1	May 9, 2013	8,502,234	Aug 6, 2013	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
13	102584-0880166	001110US	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	USA	13/935,345	Jul 3, 2013	US-2014-0159051-A1	Jun 12, 2014	8,941,117	Jan 27, 2015	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
14	102584-0928082	001120US	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	USA	14/574,265	Dec 17, 2014	US-2015-0140746-A1	May 21, 2015	9,171,937	Oct 27, 2015	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
15	102584-0816904	001300US	METHOD AND SYSTEM FOR FLOATING GUARD RINGS IN GALLIUM NITRIDE MATERIALS	USA	13/270,606	Oct 11, 2011	US-2013-0087835-A1	Apr 11, 2013	9,224,828	Dec 29, 2015	Issued	Andrew Edwards, Hui Nie, Isik C. Kizilyalli, Richard J. Brown, David P. Bour, Linda Romano, Thomas R. Prunty
16	102584-0816905	001400US	METHOD AND SYSTEM FOR DIFFUSION AND IMPLANTATION IN GALLIUM NITRIDE BASED DEVICES	USA	13/240,877	Sep 22, 2011	US-2013-0075748-A1	Mar 28, 2013	8,846,482	Sep 30, 2014	Issued	David P. Bour, Richard J. Brown, Isik C. Kizilyalli, Thomas R. Prunty, Linda Romano, Andrew P. Edwards, Hui Nie, Mahdhan Raj
17	102584-0919838	001410US	METHOD AND SYSTEM FOR DIFFUSION AND IMPLANTATION IN GALLIUM NITRIDE BASED DEVICES	USA	14/498,916	Sep 26, 2014	US-2015-0017792-A1	Jan 15, 2015	9,318,331	Apr 19, 2016	Issued	David P. Bour, Richard J. Brown, Isik C. Kizilyalli, Thomas R. Prunty, Linda Romano, Andrew P. Edwards, Hui Nie, Mahdhan Raj
18	102584-0819244	001500US	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED P-I-N SCHOTTKY (MPS) DIODE	USA	13/270,625	Oct 11, 2011	US-2013-0087878-A1	Apr 11, 2013	8,778,788	Jul 15, 2014	Issued	Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
19	102584-0909959	001510US	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED P-I-N SCHOTTKY (MPS) DIODE	USA	14/299,773	Jun 9, 2014	US-2014-0287570-A1	Sep 25, 2014	9,171,923	Oct 27, 2015	Issued	Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
20	102584-0819311	001600US	VERTICAL GAN-BASED METAL INSULATOR SEMICONDUCTOR JET	USA	13/315,705	Dec 9, 2011	US-2013-0146885-A1	Jun 13, 2013	8,558,242	Oct 15, 2013	Issued	Richard J. Brown, Hui Nie, Andrew Edwards, Isik Kizilyalli, David Bour, Thomas Prunty, Linda Romano, Mahdhan Raj
21	102584-0819313	001700US	GALLIUM NITRIDE BASED SCHOTTKY BARRIER DIODE WITH ALUMINUM GALLIUM NITRIDE SURFACE LAYER	USA	13/300,009	Nov 18, 2011	US-2013-0126886-A1	May 23, 2013	8,836,071	Sep 16, 2014	Issued	Richard J. Brown, Thomas R. Prunty, David P. Bour, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Mahdhan Raj
22	102584-0914224	001710US	GAN-BASED SCHOTTKY BARRIER DIODE WITH ALGAN SURFACE LAYER	USA	14/479,634	Sep 8, 2014	US-2014-0374769-A1	Dec 25, 2014	9,450,112	Sep 20, 2016	Issued	Richard J. Brown, Thomas R. Prunty, David P. Bour, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Mahdhan Raj
23	102584-0819312	001800US	GAN-BASED SCHOTTKY BARRIER DIODE WITH FIELD PLATE	USA	13/300,028	Nov 18, 2011	US-2013-0127006-A1	May 23, 2013	8,643,134	Feb 4, 2014	Issued	Mahdhan Raj, Richard J. Brown, Thomas R. Prunty, David P. Bour, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano
24	102584-0819315	002000US	ALUMINUM GALLIUM NITRIDE ETCH STOP LAYER FOR GALLIUM NITRIDE BASED DEVICES	USA	13/299,227	Nov 17, 2011	US-2013-0126884-A1	May 23, 2013	9,159,784	Oct 13, 2015	Issued	Linda Romano, Andrew P. Edwards, Richard J. Brown, David P. Bour, Hui Nie, Isik C. Kizilyalli, Thomas R. Prunty, Mahdhan Raj
25	102584-0880283	002010US	ALUMINUM GALLIUM NITRIDE ETCH STOP LAYER FOR GALLIUM NITRIDE BASED DEVICES	USA	13/932,290	Jul 1, 2013	US-2014-0162416-A1	Jun 12, 2014	9,093,284	Jul 28, 2015	Issued	Linda Romano, Andrew P. Edwards, Richard J. Brown, David P. Bour, Hui Nie, Isik C. Kizilyalli, Thomas R. Prunty, Mahdhan Raj
26	102584-0824390	002100US	METHOD AND SYSTEM FOR A GAN SELF-ALIGNED VERTICAL MISFET	USA	13/335,572	Dec 22, 2011	US-2013-0161635-A1	Jun 27, 2013	8,866,147	Oct 21, 2014	Issued	Richard J. Brown, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, David P. Bour
27	102584-0917598	002110US	METHOD AND SYSTEM FOR A GALLIUM NITRIDE SELF-ALIGNED VERTICAL MISFET	USA	14/489,761	Sep 18, 2014	US-2015-0179772-A1	Jun 25, 2015	9,269,793	Feb 23, 2016	Issued	Richard J. Brown, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, David P. Bour
28	102584-0819316	002200US	METHOD OF FABRICATING A GAN P-I-N DIODE USING IMPLANTATION	USA	13/335,329	Dec 22, 2011	US-2013-0161780-A1	Jun 27, 2013	8,822,311	Sep 2, 2014	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown, Donald R. Disney
29	102584-0914225	002210US	METHOD OF FABRICATING A GALLIUM NITRIDE P-I-N DIODE USING IMPLANTATION	USA	14/454,524	Aug 7, 2014	US-2014-0346527-A1	Nov 27, 2014	9,171,900	Oct 27, 2015	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown, Donald R. Disney
30	102584-0955950	002220US	METHOD OF FABRICATING A GAN P-I-N DIODE USING IMPLANTATION	USA	14/834,306	Aug 24, 2015	US-2015-0964612-A1	Dec 17, 2015	9,484,470	Nov 1, 2016	Issued	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown, Donald R. Disney
31	102584-0824393	002300US	METHOD AND SYSTEM FOR CARBON DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	USA	13/307,108	Nov 30, 2011	US-2013-0137225-A1	May 30, 2013	8,568,153	Oct 29, 2013	Issued	David P. Bour, Thomas R. Prunty, Linda Romano, Richard J. Brown, Isik C. Kizilyalli, Hui Nie
32	102584-0891183	002310US	METHOD AND SYSTEM FOR CARBON DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	USA	14/061,741	Oct 23, 2013	US-2014-0116328-A1	May 3, 2014	8,853,063	Oct 7, 2014	Issued	David P. Bour, Thomas R. Prunty, Linda Romano, Richard J. Brown, Isik C. Kizilyalli, Hui Nie
33	102584-0822319	002400US	SCHOTTKY DIODE WITH BURIED LAYER IN GAN MATERIALS	USA	13/270,641	Oct 11, 2011	US-2013-0087879-A1	Apr 11, 2013	8,933,532	Jan 13, 2015	Issued	Andrew Edwards, Hui Nie, Isik C. Kizilyalli, Richard J. Brown, David P. Bour, Linda Romano, Thomas R. Prunty
34	102584-0929734	002410US	SCHOTTKY DIODE WITH BURIED LAYER IN GAN MATERIALS	USA	14/594,778	Jan 12, 2015	US-2015-0179733-A1	Jun 25, 2015	9,196,679	Nov 24, 2015	Issued	Andrew Edwards, Hui Nie, Isik C. Kizilyalli, Richard J. Brown, David P. Bour, Linda Romano, Thomas R. Prunty
35	102584-0823950	002500US	METHOD AND SYSTEM FOR FABRICATING FLOATING GUARD RINGS IN GAN MATERIALS	USA	13/299,254	Nov 17, 2011	US-2013-0126885-A1	May 23, 2013	8,749,015	Jun 10, 2014	Issued	Donald R. Disney, Andrew P. Edwards, Hui Nie, Richard J. Brown, Isik C. Kizilyalli, David P. Bour, Linda Romano, Thomas R. Prunty
36	102584-0907687	002510US	METHOD AND SYSTEM FOR FABRICATING FLOATING GUARD RINGS IN GAN MATERIALS	USA	14/264,998	Apr 29, 2014	US-2014-0235030-A1	Aug 21, 2014	9,171,751	Oct 27, 2015	Issued	Donald R. Disney, Andrew P. Edwards, Hui Nie, Richard J. Brown, Isik C. Kizilyalli, David P. Bour, Linda Romano, Thomas R. Prunty
37	102584-0824394	002600US	FABRICATION OF FLOATING GUARD RINGS USING SELECTIVE REGROWTH	USA	13/335,355	Dec 22, 2011	US-2013-0164893-A1	Jun 27, 2013	8,592,298	Nov 26, 2013	Issued	Linda Romano, David P. Bour, Andrew Edwards, Hui Nie, Isik C. Kizilyalli, Richard J. Brown, Thomas R. Prunty
38	102584-0824395	002700US	VERTICAL GAN JET WITH GATE SOURCE ELECTRODES ON REGROWN GATE	USA	13/315,720	Dec 9, 2011	US-2013-0146886-A1	Jun 13, 2013	8,698,164	Apr 15, 2014	Issued	Donald R. Disney, Hui Nie, Isik C. Kizilyalli, Richard J. Brown
39	102584-0902003	002710US	VERTICAL GALLIUM NITRIDE JET WITH GATE AND SOURCE ELECTRODES ON REGROWN GATE	USA	14/192,662	Feb 27, 2014	US-2014-0293165-A1	Oct 2, 2014	8,946,725	Feb 3, 2015	Issued	Donald R. Disney, Hui Nie, Isik C. Kizilyalli, Richard J. Brown
40	102584-0933414	002720US	VERTICAL GALLIUM NITRIDE JET WITH GATE AND SOURCE ELECTRODES ON REGROWN GATE	USA	14/606,822	Jan 27, 2015	US-2015-0137140-A1	May 21, 2015	9,318,619	Apr 13, 2016	Issued	Donald R. Disney, Hui Nie, Isik C. Kizilyalli, Richard J. Brown
41	102584-0826382	002800US	METHOD AND SYSTEM FOR JUNCTION TERMINATION IN GAN MATERIALS USING CONDUCTIVITY MODULATION	USA	13/334,742	Dec 22, 2011	US-2013-0161633-A1	Jun 27, 2013	8,716,716	May 6, 2014	Issued	Hui Nie, Andrew P. Edwards, Donald R. Disney, Richard J. Brown, Isik C. Kizilyalli
42	102584-0904471	002810US	METHOD AND SYSTEM FOR JUNCTION TERMINATION IN GAN MATERIALS USING CONDUCTIVITY MODULATION	USA	14/220,564	Mar 20, 2014	US-2014-0206179-A1	Jul 24, 2014	8,969,180	Mar 3, 2015	Issued	Hui Nie, Andrew P. Edwards, Donald R. Disney, Richard J. Brown, Isik C. Kizilyalli
43	102584-0826381	002900US	METHOD AND SYSTEM FOR PLANAR REGROWTH IN GAN ELECTRONIC DEVICES	USA	13/465,812	May 7, 2012	US-2013-0292686-A1	Nov 7, 2013	9,117,839	Aug 25, 2015	Issued	Isik C. Kizilyalli, Linda Romano, David P. Bour
44	102584-0952881	002910US	METHOD AND SYSTEM FOR PLANAR REGROWTH IN GAN ELECTRONIC DEVICES	USA	14/815,780	Jul 31, 2015	US-2015-0340476-A1	Nov 26, 2015	9,502,544	Nov 22, 2016	Issued	Isik C. Kizilyalli, Linda Romano, David P. Bour
45	102584-0826380	003000US	METHOD AND SYSTEM FOR A GAN VERTICAL JET WITH SELF-ALIGNED SOURCE AND GATE	USA	13/334,514	Dec 22, 2011	US-2013-0161705-A1	Jun 27, 2013	8,829,574	Sep 9, 2014	Issued	Donald R. Disney, Isik C. Kizilyalli, Hui Nie, Linda Romano, Richard J. Brown, Mahdhan Raj
46	102584-0914237	003010US	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL JET WITH SELF-ALIGNED SOURCE AND GATE	USA	14/471,374	Aug 28, 2014	US-2014-0370669-A1	Dec 18, 2014	9,117,850	Aug 25, 2015	Issued	Don Disney, Isik C. Kizilyalli, Hui Nie, Linda Romano, Richard J. Brown, Mahdhan Raj
47	102584-0826379	003100US	METHOD AND SYSTEM FOR FABRICATING EDGE TERMINATION STRUCTURES IN GAN MATERIALS	USA	13/335,383	Dec 22, 2011	US-2013-0161634-A1	Jun 27, 2013	8,741,707	Jun 3, 2014	Issued	Donald R. Disney, Isik C. Kizilyalli, Linda Romano, Andrew P. Edwards, Hui Nie
48	102584-0833448	003200US	GAN VERTICAL SUPERJUNCTION DEVICE STRUCTURES AND FABRICATION METHODS	USA	13/529,822	Jun 21, 2012	US-2013-0341677-A1	Dec 26, 2013	8,785,975	Jul 22, 2014	Issued	Hui Nie, Andrew P. Edwards, Donald R. Disney, Isik C. Kizilyalli
49	102584-0911269	003210US	GAN VERTICAL SUPERJUNCTION DEVICE STRUCTURES AND FABRICATION METHODS	USA	14/302,270	Jun 11, 2014	US-2014-0295652-A1	Oct 2, 2014	9,020,210	May 12, 2015	Issued	Hui Nie, Andrew P. Edwards, Donald R. Disney, Isik C. Kizilyalli
50	102584-0833449	003300US	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL JET WITH SELF-ALIGNED GATE METALLIZATION	USA	13/468,325	May 10, 2012	US-2013-0299873-A1	Nov 14, 2013	8,716,078	May 6, 2014	Issued	Donald R. Disney, Richard J. Brown, Hui Nie
51	102584-0839418	003310US	METHOD AND SYSTEM FOR A GAN VERTICAL JET WITH SELF-ALIGNED SOURCE METALLIZATION	USA	13/468,332	May 10, 2012	US-2013-0299882-A1	Nov 14, 2013	8,841,708	Sep 23, 2014	Issued	Donald R. Disney, Richard J. Brown, Hui Nie
52	102584-0833463	003400US	VERTICAL GAN JET WITH LOW GATE-DRAIN CAPACITANCE AND HIGH GATE-SOURCE CAPACITANCE	USA	13/675,694	Nov 13, 2012	US-2014-0131775-A1	May 15, 2014	8,969,926	Mar 3, 2015	Issued	Donald R. Disney
53	102584-0929266	003410US	VERTICAL GAN JET WITH LOW GATE-DRAIN CAPACITANCE AND HIGH GATE-SOURCE CAPACITANCE	USA	14/604,606	Jan 23, 2015	US-2015-0132900-A1	May 14, 2015	9,391,179	Jul 12, 2016	Issued	Donald R. Disney
54	102584-0840540	003500US	GAN POWER DEVICE WITH SOLDERABLE BACK METAL	USA	13/552,365	Jul 18, 2012	US-2014-0021479-A1	Jan 23, 2014	9,105,579	Aug 11, 2015	Issued	Patrick James Lazlo Hyland, Brian Joel Alvarez, Donald R. Disney
55	102584-0952880	003510US	GAN POWER DEVICE WITH SOLDERABLE BACK METAL	USA	14/815,751	Jul 31, 2015	US-2015-0340271-A1	Nov 26, 2015	9,324,607	Apr 26, 2016	Issued	Patrick James Lazlo Hyland, Brian Joel Alvarez, Donald R. Disney
56	102584-0840541	003600US	METHOD AND SYSTEM FOR GALLIUM NITRIDE ELECTRONIC DEVICES USING ENGINEERED SUBSTRATES	USA	13/572,408	Aug 10, 2012	US-2014-0042447-A1	Feb 13, 2014	8,981,432	Mar 17, 2015	Issued	Hui Nie, Donald R. Disney, Isik C. Kizilyalli
57	102584-0840543	003800US	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED P-I-N SCHOTTKY (MPS) DIODE BY REGROWTH AND ETCH BACK	USA	13/585,121	Aug 14, 2012	US-2014-0048902-A1	Feb 20, 2014	8,969,994	Mar 3, 2015	Issued	Mahdhan Raj, Brian Alvarez, David P. Bour, Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli

EXHIBIT A
Nexgen ABC Patents

#	FILE NO.	IP FAMILY NO.	TITLE	COUNTRY	APPLN. NO.	FILING DATE	PUB. NO.	PUB. DATE	PATENT NO.	ISSUE DATE	STATUS	INVENTORS
58	102584-0925703	003801US	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED P-N SCHOTTKY (MPS) DIODE BY REGROWTH AND ETCH BACK	USA	14/602,125	Jan 21, 2015	US-2015-0200268-A1	Jul 16, 2015	9,397,186	Jul 19, 2016	Issued	Madhan M. Raj, Brian Alvarez, David P. Bour, Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli
59	102584-0843972	003900US	BONDABLE TOP METAL CONTACTS FOR GALLIUM NITRIDE POWER DEVICES	USA	13/611,467	Sep 12, 2012	US-2014-0070226-A1	Mar 13, 2014	8,916,871	Dec 23, 2014	Issued	Brian Joel Alvarez, Donald R. Disney, Hui Nie, Patrick James Lario Hyland
60	102584-0843971	004000US	AC-DC CONVERTER FOR WIDE RANGE OUTPUT VOLTAGE AND HIGH SWITCHING FREQUENCY	USA	13/692,717	Dec 3, 2012	US-2014-0153304-A1	Jun 5, 2014	9,089,083	Jul 21, 2015	Issued	Sithipong Angkittrakul, Hemal N. Shah
61	102584-0951416	004010US	AC-DC CONVERTER FOR WIDE RANGE OUTPUT VOLTAGE AND HIGH SWITCHING FREQUENCY	USA	14/803,552	Jul 20, 2015	US-2015-0326140-A1	Nov 12, 2015	9,369,059	Jun 14, 2016	Issued	Sithipong Angkittrakul, Hemal N. Shah
62	102584-0843980	004100US	METHOD AND SYSTEM FOR IN-SITU ETCH AND REGROWTH IN GALLIUM NITRIDE BASED DEVICES	USA	13/571,743	Aug 10, 2012	US-2014-0045306-A1	Feb 13, 2014	9,123,533	Sep 1, 2015	Issued	David P. Bour, Thomas R. Prunty, Hui Nie, Madhan M. Raj
63	102584-1059424	004120US	METHOD AND SYSTEM FOR IN-SITU ETCH AND REGROWTH IN GALLIUM NITRIDE BASED DEVICES	USA	15/681,823	Aug 21, 2017	US-2018-0190789-A1	Jul 5, 2018	10,319,829	Jun 11, 2019	Issued	David P. Bour, Thomas R. Prunty, Hui Nie, Madhan M. Raj
64	102584-0851061	004200US	GAN VERTICAL BIPOLAR TRANSISTOR	USA	13/675,916	Nov 13, 2012	US-2014-0131837-A1	May 15, 2014	8,823,140	Sep 2, 2014	Issued	Hui Nie, Andrew Edwards, Isik Kizilyalli, Dave Bour
65	102584-0851059	004400US	LATERAL GAN JFET WITH VERTICAL DRIFT REGION	USA	13/675,826	Nov 13, 2012	US-2014-0131721-A1	May 15, 2014	9,472,684	Oct 18, 2016	Issued	Hui Nie, Andrew Edwards, Isik Kizilyalli, Dave Bour, Thomas R. Prunty
66	102584-0856301	004700US	METHOD AND SYSTEM FOR CO-PACKAGING GALLIUM NITRIDE ELECTRONICS	USA	13/730,619	Dec 28, 2012	US-2014-0183543-A1	Jul 3, 2014	8,937,317	Jan 20, 2015	Issued	Donald R. Disney, Hemal N. Shah
67	102584-0856300	004800US	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL TRANSISTOR	USA	13/735,912	Jan 7, 2013	US-2014-0191242-A1	Jul 10, 2014	9,059,199	Jun 16, 2015	Issued	Hui Nie, Andrew P. Edwards, Isik Kizilyalli, David P. Bour, Thomas R. Prunty, Quentin Dioduck
68	102584-0856302	004900US	VERTICAL GAN POWER DEVICE WITH BREAKDOWN VOLTAGE CONTROL	USA	13/721,542	Dec 20, 2012	US-2014-0175450-A1	Jun 26, 2014	8,866,148	Oct 21, 2014	Issued	Donald R. Disney
69	102584-0919839	004910US	VERTICAL GALLIUM NITRIDE POWER DEVICE WITH BREAKDOWN VOLTAGE CONTROL	USA	14/517,564	Oct 17, 2014	US-2015-0104912-A1	Apr 16, 2015	9,257,500	Feb 9, 2016	Issued	Donald R. Disney
70	102584-0868145	005000US	GALLIUM NITRIDE FIELD EFFECT TRANSISTOR WITH BURIED FIELD PLATE PROTECTED LATERAL CHANNEL	USA	14/077,039	Nov 11, 2013	US-2015-0129886-A1	May 14, 2015	9,123,799	Sep 1, 2015	Issued	Ozgur Aktas, Isik C. Kizilyalli
71	102584-0868147	005200US	METHOD OF FABRICATING A MERGED P-N JUNCTION AND SCHOTTKY DIODE WITH REGROWN GALLIUM NITRIDE LAYER	USA	13/866,286	Apr 19, 2013	US-2014-0312355-A1	Oct 23, 2014	9,159,799	Oct 13, 2015	Issued	Isik C. Kizilyalli, Dave P. Bour, Thomas R. Prunty, Hui Nie, Quentin Dioduck, Ozgur Aktas
72	102584-0958526	005210US	METHOD OF FABRICATING A MERGED P-N JUNCTION AND SCHOTTKY DIODE WITH REGROWN GALLIUM NITRIDE LAYER	USA	14/853,930	Sep 14, 2015	US-2016-0005835-A1	Jan 7, 2016	9,525,039	Dec 20, 2016	Issued	Isik C. Kizilyalli, Dave P. Bour, Thomas R. Prunty, Hui Nie, Quentin Dioduck, Ozgur Aktas
73	102584-0873690	005300US	METHOD AND SYSTEM FOR CO-PACKAGING VERTICAL GALLIUM NITRIDE POWER DEVICES	USA	13/901,546	May 23, 2013	US-2014-0346522-A1	Nov 27, 2014	9,324,645	Apr 26, 2016	Issued	Donald R. Disney, Hemal N. Shah
74	102584-0873691	005400US	METHOD AND SYSTEM FOR OPERATING GALLIUM NITRIDE ELECTRONICS	USA	14/045,708	Oct 3, 2013			8,947,154	Feb 3, 2015	Issued	Hemal N. Shah, Donald R. Disney, Heratch Amirkhani Namagardi
75	102584-0875610	005500US	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	USA	14/071,032	Nov 4, 2013	US-2015-0123138-A1	May 7, 2015	9,368,582	Jun 14, 2016	Issued	Isik C. Kizilyalli, David P. Bour, Thomas R. Prunty, Gangfeng Ye
76	102584-1060562	005520US	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	USA	15/697,161	Sep 6, 2017	US-2018-0166556-A1	Jun 14, 2018	10,347,736	Jul 9, 2019	Issued	Isik C. Kizilyalli, Dave P. Bour, Thomas R. Prunty, Gangfeng Ye
77	102584-1138575	005530US	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	USA	16/423,414	May 28, 2019	US-2019-0348522-A1	Nov 14, 2019	10,566,439	Feb 18, 2020	Issued	Isik C. Kizilyalli, Dave P. Bour, Thomas R. Prunty, Gangfeng Ye
78	102584-1173882	005540US	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	USA	16/789,781	Feb 13, 2020	US-2020-0279695-A1	Aug 27, 2020	10,854,727	Dec 1, 2020	Issued	Isik C. Kizilyalli, Dave P. Bour, Thomas R. Prunty, Gangfeng Ye
79	102584-0875611	005600US	AC-DC CONVERTER WITH ADJUSTABLE OUTPUT	USA	14/095,759	Dec 3, 2013	US-2015-0155775-A1	Jun 4, 2015	9,531,256	Dec 27, 2016	Issued	Hemal N. Shah, Vinod Khosla
80	102584-0880156	005700US	METHOD AND SYSTEM FOR INTERLEAVED BOOST CONVERTER WITH CO-PACKAGED GALLIUM NITRIDE POWER DEVICES	USA	14/083,217	Nov 18, 2013	US-2015-0137134-A1	May 21, 2015	9,324,809	Apr 26, 2016	Issued	Hemal N. Shah, Donald R. Disney
81	102584-1060561	005830US	ADAPTIVE SYNCHRONOUS SWITCHING IN A RESONANT CONVERTER	USA	15/697,170	Sep 6, 2017	US-2018-0166997-A1	Jun 14, 2018	10,256,741	Apr 9, 2019	Issued	Antoin Russell, Alberto Doronzo
82	102584-0909227	006400US	POWER SUPPLY	USA	29/501,217	Sep 2, 2014			D728,475	May 5, 2015	Issued	Yves Behar, Noah Murphy-Reinhertz, Diana Chang, Darin Smedberg, Frederick Allen Stillman
83	102584-0943796	006410US	POWER SUPPLY	USA	29/525,732	May 1, 2015			D762,573	Aug 2, 2016	Issued	Yves Behar, Noah Murphy-Reinhertz, Diana Chang, Darin Smedberg, Frederick Allen Stillman
84	102584-1202343	006910US	METHOD AND SYSTEM FOR FABRICATION OF A VERTICAL FIN-BASED FIELD EFFECT TRANSISTOR	USA	16/929,926	Jul 15, 2020	US-2021-0028312-A1	Jan 28, 2021	11,335,810	May 17, 2022	Issued	Clifford Drowley, Ray Milano, Subhash Srinivas Pidaparathi, Andrew P. Edwards, Hao Cui, Shahin Sharifzadeh
85	102584-1300307	006920US	METHOD AND SYSTEM FOR FABRICATION OF A VERTICAL FIN-BASED FIELD EFFECT TRANSISTOR	USA	17/719,221	Apr 12, 2022	US-2022-0310843-A1	Sep 29, 2022	11,735,671	Aug 22, 2023	Issued	Clifford Drowley, Ray Milano, Subhash Srinivas Pidaparathi, Andrew P. Edwards, Hao Cui, Shahin Sharifzadeh
86	102584-1392052	006930US	METHOD AND SYSTEM FOR FABRICATION OF A VERTICAL FIN-BASED FIELD EFFECT TRANSISTOR	USA	18/213,781	Jun 23, 2023	US-2023-0411525-A1	Dec 21, 2023			Published	Clifford Drowley, Ray Milano, Subhash Srinivas Pidaparathi, Andrew P. Edwards, Hao Cui, Shahin Sharifzadeh
87	102584-1213619	007010US	METHOD AND SYSTEM FOR JFET WITH IMPLANT ISOLATION	USA	17/131,568	Dec 22, 2020	US-2021-0193846-A1	Jun 24, 2021	11,637,209	Apr 25, 2023	Issued	Clifford Drowley, Andrew P. Edwards, Subhash Srinivas Pidaparathi, Ray Milano
88	102584-0933382	007020US	FABRICATION METHOD FOR JFET WITH IMPLANT ISOLATION	USA	18/119,717	Mar 9, 2023	US-2023-0215958-A1	Jul 6, 2023			Allowed	Clifford Drowley, Andrew P. Edwards, Subhash Srinivas Pidaparathi, Ray Milano
89	102584-1219654	007110US	REGROWTH UNIFORMITY IN GAN VERTICAL DEVICES	USA	17/135,436	Dec 28, 2020	US-2021-0210624-A1	Jul 8, 2021			Allowed	Clifford Drowley, Ray Milano, Subhash Srinivas Pidaparathi, Andrew P. Edwards
90	102584-1411128	007120US	REGROWTH UNIFORMITY IN GAN VERTICAL DEVICES	USA							Unfiled	Clifford Drowley, Ray Milano, Subhash Srinivas Pidaparathi, Andrew P. Edwards
91	102584-1202342	007310US	METHOD AND SYSTEM FOR FABRICATING FIDUCIALS USING SELECTIVE AREA GROWTH	USA	16/929,896	Jul 15, 2020	US-2021-0020580-A1	Jan 21, 2021	11,315,884	Apr 26, 2022	Issued	Clifford Drowley, Ray Milano, Robert Routh, Subhash Srinivas Pidaparathi, Andrew P. Edwards
92	102584-1304097	007320US	METHOD AND SYSTEM FOR FABRICATING FIDUCIALS USING SELECTIVE AREA GROWTH	USA	17/707,833	Mar 29, 2022	US-2022-0293530-A1	Sep 15, 2022			Allowed	Clifford Drowley, Ray Milano, Robert Routh, Subhash Srinivas Pidaparathi, Andrew P. Edwards
93	102584-1253600	007410US	SUPERJUNCTION BASED VERTICAL GALLIUM NITRIDE JFET POWER DEVICES	USA	17/350,237	Jun 17, 2021	US-2021-0399091-A1	Dec 23, 2021	11,575,000	Feb 7, 2023	Issued	Hao Cui, Clifford Drowley
94	102584-1365433	007420US	METHOD OF FABRICATING SUPER-JUNCTION BASED VERTICAL GALLIUM NITRIDE JFET AND MOSFET POWER DEVICES	USA	18/085,985	Dec 21, 2022	US-2023-0127978-A1	Apr 27, 2023	11,824,086	Nov 21, 2023	Issued	Hao Cui, Clifford Drowley
95	102584-1410103	007430US	METHOD OF FABRICATING SUPER-JUNCTION BASED VERTICAL GALLIUM NITRIDE JFET AND MOSFET POWER DEVICES	USA	18/371,956	Sep 22, 2023					Pending	Hao Cui, Clifford Drowley
96	102584-1253606	007510US	METHOD AND SYSTEM FOR ETCH DEPTH CONTROL IN ILLY SEMICONDUCTOR DEVICES	USA	17/956,042	Jun 23, 2021	US-2021-0407815-A1	Dec 30, 2021			Allowed	Wayne Chen, Andrew P. Edwards, Clifford Drowley, Subhash Srinivas Pidaparathi
97	102584-1242401	007610US	METHOD FOR REGROWN SOURCE CONTACTS FOR VERTICAL GALLIUM NITRIDE BASED FETS	USA	17/211,562	Mar 24, 2021	US-2021-0305404-A1	Sep 30, 2021	11,728,415	Aug 15, 2023	Issued	Clifford Drowley, Andrew P. Edwards, Subhash Srinivas Pidaparathi, Shahin Sharifzadeh
98	102584-1391276	007620US	VERTICAL GALLIUM NITRIDE BASED FETS WITH REGROWN SOURCE CONTACTS	USA	18/213,707	Jun 23, 2023	US-2023-0420547-A1	Dec 28, 2023			Published	Clifford Drowley, Andrew P. Edwards, Subhash Srinivas Pidaparathi, Shahin Sharifzadeh
99	102584-1254428	007710US	METHOD AND SYSTEM OF JUNCTION TERMINATION EXTENSION IN HIGH VOLTAGE SEMICONDUCTOR DEVICES	USA	17/369,600	Jul 7, 2021	US-2022-0013626-A1	Jan 13, 2022			Published	Subhash Srinivas Pidaparathi, Andrew P. Edwards, Clifford Drowley, Kedar Patel
100	102584-1254455	007810US	SELF-ALIGNED ISOLATION FOR SELF-ALIGNED CONTACTS FOR VERTICAL FETS	USA	17/973,627	Jul 12, 2021	US-2022-0020743-A1	Jan 20, 2022			Published	Clifford Drowley, Hao Cui, Andrew P. Edwards, Subhash Srinivas Pidaparathi
101	102584-1267250	007910US	NONLINEAR, DISCRETE TIME CONTROL OF POWER FACTOR CORRECTION POWER CONVERTER	USA	17/524,030	Nov 11, 2021	US-2022-0158546-A1	May 19, 2022			Published	Anders Lind
102	102584-1282352	007920US	METHOD AND SYSTEM FOR CONTROLLING THE POWER FACTOR OF A POWER CONVERTER	USA	17/524,064	Nov 11, 2021	US-2022-0158547-A1	May 19, 2022			Allowed	Anders Lind
103	102584-1267257	008010US	METHOD AND SYSTEM FOR ENTERING AND EXITING A FREQUENCY CLAMP MODE FOR VARIABLE FREQUENCY, OFFLINE SWITCH-MODE POWER CONVERTERS	USA	17/524,067	Nov 11, 2021	US-2022-0158559-A1	May 19, 2022			Published	Anders Lind
104	102584-1267234	008110US	SELF-OSCILLATING HIGH FREQUENCY CONVERTER WITH POWER FACTOR CORRECTION	USA	17/498,426	Oct 11, 2021	US-2022-0149720-A1	May 12, 2022	11,837,951	Dec 5, 2023	Issued	Charles Coles
105	102584-1267254	008210US	METHOD AND APPARATUS FOR DIGITAL, CLOSED-LOOP CONTROL OF CRCM SWITCH-MODE POWER CONVERTERS	USA	17/524,117	Nov 11, 2021	US-2022-0158560-A1	May 19, 2022	11,770,075	Sep 26, 2023	Issued	Anders Lind
106	102584-1400002	008211US	METHOD AND APPARATUS FOR DIGITAL, CLOSED-LOOP CONTROL OF CRCM SWITCH-MODE POWER CONVERTERS	USA	18/233,255	Aug 11, 2023					Pending	Anders Lind
107	102584-1282355	008220US	METHOD AND APPARATUS FOR OVER-CURRENT PROTECTION AND CRCM CONTROL IN POWER CONVERTERS	USA	17/524,126	Nov 11, 2021	US-2022-0158561-A1	May 19, 2022			Published	Anders Lind
108	102584-1282361	008230US	METHOD AND APPARATUS FOR SENSING THE INPUT VOLTAGE OF A POWER CONVERTER	USA	17/524,136	Nov 11, 2021	US-2022-0158539-A1	May 19, 2022	11,824,430	Nov 21, 2023	Issued	Anders Lind
109	102584-1396929	008231US	METHOD AND APPARATUS FOR SENSING THE INPUT VOLTAGE OF A POWER CONVERTER	USA	18/371,332	Sep 21, 2023					Pending	Anders Lind
110	102584-1300275	008310US	METHODS AND SYSTEMS FOR FABRICATION OF VERTICAL FIN-BASED JFETS	USA	17/667,432	Feb 8, 2022	US-2022-0254918-A1	Aug 11, 2022			Published	Clifford Drowley, Hao Cui, Andrew P. Edwards, Subhash Srinivas Pidaparathi
111	102584-1294934	008410US	COUPLED GUARD RINGS FOR EDGE TERMINATION	USA	17/584,215	Jan 25, 2022	US-2022-0328643-A1	Jul 28, 2022			Published	Clifford Drowley, Andrew P. Edwards, Hao Cui, Subhash Srinivas Pidaparathi
112	102584-1300317	008510US	METHOD AND SYSTEM FOR CONTROL OF SIDEWALL ORIENTATION IN VERTICAL GALLIUM NITRIDE FIELD EFFECT TRANSISTORS	USA	17/707,835	Mar 29, 2022	US-2022-0328688-A1	Oct 13, 2022			Published	Clifford Drowley, Andrew P. Edwards, Hao Cui, Subhash Srinivas Pidaparathi, Michael Craven, David DeMuynek
113	102584-1300316	008610US	METHODS AND SYSTEMS TO IMPROVE UNIFORMITY IN POWER FET ARRAYS	USA	17/707,839	Mar 29, 2022	US-2022-0328476-A1	Oct 13, 2022			Published	Clifford Drowley, Andrew P. Edwards, Hao Cui, Subhash Srinivas Pidaparathi
114	102584-1371858	008710US	VERTICAL FIN-BASED FIELD EFFECT TRANSISTOR (VFNET) WITH VARYING CONDUCTIVITY REGIONS	USA	18/108,457	Feb 10, 2023	US-2023-0260996-A1	Aug 17, 2023			Published	Clifford Drowley, Andrew J. Walker, Andrew P. Edwards, Subhash Srinivas Pidaparathi

EXHIBIT A
Nexgen ABC Patents

#	FILE NO.	IP FAMILY NO.	TITLE	COUNTRY	APPLN. NO.	FILING DATE	PUB. NO.	PUB. DATE	PATENT NO.	ISSUE DATE	STATUS	INVENTORS
115	102584-1380932	008810US	NEGATIVE CHARGE EXTRACTION STRUCTURE FOR EDGE TERMINATION	USA	18/137,329	Apr 20, 2023					Pending	Kyoung Wook Seok, Clifford Drowley, Andrew J. Walker, Andrew P. Edwards
116	102584-1362421	008910US	A VERTICAL FIN-BASED FIELD EFFECT TRANSISTOR (FINFET) WITH NEUTRALIZED FIN TIPS	USA	18/097,693	Jan 17, 2023	US-2023-0246027-A1	Aug 3, 2023			Published	Subhash Srinivas Pidaparthi, Clifford Drowley, Shahin Sharifzadeh, Andrew P. Edwards, Andrew Walker, Francis Chai
117	102584-1362419	009010US	METHOD AND SYSTEM FOR FABRICATING REGROWN FIDUCIALS FOR SEMICONDUCTOR DEVICES	USA	18/097,683	Jan 17, 2023	US-2023-0230931-A1	Jul 20, 2023			Published	Karthik Suresh Anulalan, Jianfeng Wang, Sharlene Wilson, Mark Curtice, Subhash Srinivas Pidaparthi, Clifford Drowley
118	102584-1362420	009110US	METHOD AND SYSTEM FOR FABRICATING FIDUCIALS FOR PROCESSING OF SEMICONDUCTOR DEVICES	USA	18/097,994	Jan 17, 2023	US-2023-0230932-A1	Jul 20, 2023			Published	David DeMuyne, Subhash Srinivas Pidaparthi, Sharlene Wilson, Karthik Suresh Anulalan, Mark Curtice, Andrew P. Edwards, Clifford Drowley
119	102584-1327962	009210US	METHOD AND SYSTEM FOR FIN-BASED VOLTAGE CLAMP	USA	18/137,314	Apr 20, 2023	US-2023-0378750-A1	Nov 23, 2023			Published	Andrew J. Walker, Clifford Drowley, Subhash Srinivas Pidaparthi, Andrew P. Edwards, Shahin Sharifzadeh, Joseph Tandinjan
120	102584-1380939	009310US	VERTICAL FIN-BASED FIELD EFFECT TRANSISTOR (FINFET) WITH CONNECTED FIN TIPS	USA	18/137,093	Apr 20, 2023	US-2023-0361126-A1	Nov 9, 2023			Published	Andrew P. Edwards, Andrew J. Walker, Clifford Drowley, Subhash Srinivas Pidaparthi
121	102584-1380941	009410US	METHOD AND SYSTEM FOR ROUTING OF ELECTRICAL CONDUCTORS OVER NEUTRALIZED POWER FETS	USA	18/137,075	Apr 20, 2023	US-2023-0378348-A1	Nov 23, 2023			Published	Clifford Drowley, Andrew J. Walker, Andrew P. Edwards, Subhash Srinivas Pidaparthi, Thomas E. Kopley
122	102584-1125503	009700US	TBD	USA							Unfiled	Clifford Drowley, Ray Milano, Subhash Srinivas Pidaparthi, Andrew P. Edwards
123	102584-1004304	005500KR	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	Korea	10-2016-7014318	Nov 3, 2014	20160079847	Jul 6, 2016	10-2257666	May 24, 2021	Issued	Isk C. Kizilyalli, David P. Bour, Thomas R. Prunty, Gangfeng Ye
124	102584-1253466	005510KR	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	Korea	10-2021-7015543	Nov 3, 2014	20210062743	May 31, 2021	10-2393431	Apr 27, 2022	Issued	David P. Bour, Isk C. Kizilyalli, Thomas R. Prunty, Gangfeng Ye
125	102584-1004303	005500JP	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	Japan	2016-552493	Nov 3, 2014	2016537831	Dec 1, 2016	6857290	Mar 24, 2021	Issued	Isk C. Kizilyalli, David P. Bour, Thomas R. Prunty, Gangfeng Ye
126	102584-1130018	005510JP	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	Japan	2019-040118	Nov 3, 2014	2019149549	Sep 5, 2019	6857786	Mar 25, 2021	Issued	Isk C. Kizilyalli, David P. Bour, Thomas R. Prunty, Gangfeng Ye
127	102584-1359160	005530JP	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	Japan	2022-178273	Nov 3, 2014					Pending	Isk C. Kizilyalli, David P. Bour, Thomas R. Prunty, Gangfeng Ye
128	102584-0899367	000710CN	METHOD AND SYSTEM FOR A GAN VERTICAL JFET UTILIZING A REGROWN CHANNEL	China	201280044944.8	Aug 3, 2012	CN 103875075A	Jun 18, 2014	ZL 201280044944.8	Sep 8, 2017	Issued	Isk C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, David P. Bour, Richard J. Brown, Thomas R. Prunty
129	102584-0908456	002500CN	METHOD AND SYSTEM FABRICATING FLOATING GUARD RINGS IN GAN MATERIALS	China	201280063052.2	Oct 31, 2012	CN 104011865A	Aug 27, 2014	ZL 201280063052.2	Apr 24, 2018	Issued	Donald R. Disney, Andrew P. Edwards, Hui Nie, Richard J. Brown, Isk C. Kizilyalli, David P. Bour, Linda Romano, Thomas R. Prunty
130	102584-1079208	002510CN	METHOD AND SYSTEM FABRICATING FLOATING GUARD RINGS IN GAN MATERIALS	China	201810244937.1	Oct 31, 2012	CN 108538717A	Sep 14, 2018	ZL 201810244937.1	Jul 12, 2022	Issued	Donald R. Disney, Andrew P. Edwards, Hui Nie, Richard J. Brown, Isk C. Kizilyalli, David P. Bour, Linda Romano, Thomas R. Prunty
131	102584-0933464	003600CN	METHOD AND SYSTEM FOR GALLIUM NITRIDE ELECTRONIC DEVICES USING ENGINEERED SUBSTRATES	China	201380042559.4	Aug 6, 2013	CN 104541373A	Apr 22, 2015	ZL 201380042559.4	Jun 8, 2018	Issued	Hui Nie, Donald R. Disney, Isk C. Kizilyalli
132	102584-1086747	003610CN	METHOD AND SYSTEM FOR GALLIUM NITRIDE ELECTRONIC DEVICES USING ENGINEERED SUBSTRATES	China	201810456225.6	Aug 6, 2013	CN 108538711A	Sep 14, 2018	ZL 201810456225.6	Jun 16, 2023	Issued	Hui Nie, Donald R. Disney, Isk C. Kizilyalli
133	102584-0944366	004400CN	LATERAL GAN JFET WITH VERTICAL DRIFT REGION	China	201380059315.7	Nov 11, 2013	CN 105103295A	Nov 25, 2015	ZL 201380059315.7	Oct 16, 2018	Issued	Hui Nie, Andrew P. Edwards, Isk C. Kizilyalli, Dave P. Bour, Thomas R. Prunty
134	102584-0946942	004800CN	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL TRANSISTOR	China	201380069597.9	Dec 18, 2013	CN 104904019A	Sep 9, 2015	ZL 201380069597.9	Sep 6, 2019	Issued	Hui Nie, Andrew P. Edwards, Isk C. Kizilyalli, Dave P. Bour, Thomas R. Prunty, Quentin Diduck
135	102584-0960353	005200CN	METHOD OF FABRICATING A MERGED P-N JUNCTION AND SCHOTTKY DIODE WITH REGROWN GALLIUM NITRIDE LAYER	China	201480021877.7	Apr 9, 2014	CN 105144392A	Dec 9, 2015	ZL 201480021877.7	May 17, 2019	Issued	Isk C. Kizilyalli, David P. Bour, Thomas R. Prunty, Hui Nie, Quentin Diduck, Oguz AKTAS
136	102584-1004302	005500CN	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	China	201480060457.X	Nov 3, 2014	CN 105765725 A	Jul 13, 2016	ZL 201480060457.X	Apr 17, 2020	Issued	Isk C. Kizilyalli, David P. Bour, Thomas R. Prunty, Gangfeng Ye
137	102584-1181634	005510CN	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCT SUBSTRATES	China	202010274985.2	Nov 3, 2014	CN 111554752A	Aug 18, 2020			Published	Isk C. Kizilyalli, David P. Bour, Thomas R. Prunty, Gangfeng Ye
138	102584-0972027	006310CN	A VARIABLE OUTPUT POWER SUPPLY AND OPERATING METHOD THEREOF	China	201610085380.2	Feb 15, 2016	CN105897006A	Aug 24, 2016	ZL 201610085380.2	Dec 24, 2021	Issued	Dinesh Ramnathan, Rob Levine, Mikhal Guz, Isk Kizilyalli
139	102584-1202341	006910CN	METHOD AND SYSTEM FOR FABRICATION OF A VERTICAL FIN-BASED FIELD EFFECT TRANSISTOR	China	202010713496.2	Jul 22, 2020	CN 112289847 A	Jan 29, 2021			Published	Clifford Drowley, Ray Milano, Subhash Srinivas Pidaparthi, Andrew P. Edwards, Hao Cui, Shahin Sharifzadeh
140	102584-1219621	007010CN	METHOD AND SYSTEM FOR JFET WITH IMPLANT ISOLATION	China	202011543305.9	Dec 23, 2020	113097296	Jul 9, 2021			Published	Clifford Drowley, Andrew P. Edwards, Subhash Srinivas Pidaparthi, Ray Milano
141	102584-1219653	007110CN	REGROWTH UNIFORMITY IN GAN VERTICAL DEVICES	China	202011618830.2	Dec 31, 2020	CN 113140560 A	Jul 20, 2021			Published	Clifford Drowley, Ray Milano, Subhash Srinivas Pidaparthi, Andrew P. Edwards
142	102584-1202344	007310CN	METHOD AND SYSTEM FOR FABRICATING FIDUCIALS USING SELECTIVE AREA GROWTH	China	202010594725.0	Jul 17, 2020	CN 112242354A	Jan 19, 2021			Published	Clifford Drowley, Ray Milano, Robert Routh, Subhash Srinivas Pidaparthi, Andrew P. Edwards
143	102584-1253601	007410CN	METHOD AND SYSTEM FOR SUPER-JUNCTION BASED VERTICAL GALLIUM NITRIDE JFET AND MOSFET POWER DEVICES	China	202110674239.7	Jun 17, 2021	CN113823565A	Dec 21, 2021			Published	Hao Cui, Clifford Drowley
144	102584-1253610	007510CN	METHOD AND SYSTEM FOR ETCH DEPTH CONTROL IN BIV SEMICONDUCTOR DEVICES	China	202110680858.X	Jun 21, 2021	CN 113851381 A	Dec 28, 2021			Published	Wayne Chen, Andrew P. Edwards, Clifford Drowley, Subhash Srinivas Pidaparthi
145	102584-1242195	007610CN	METHOD AND SYSTEM FOR REGROWN SOURCE CONTACTS FOR VERTICAL GALLIUM NITRIDE BASED FETS	China	202110322341.0	Mar 25, 2021	CN 113517228 A	Oct 19, 2021			Published	Clifford Drowley, Andrew P. Edwards, Subhash Srinivas Pidaparthi, Shahin Sharifzadeh
146	102584-1254434	007710CN	METHOD AND SYSTEM OF JUNCTION TERMINATION EXTENSION IN HIGH VOLTAGE SEMICONDUCTOR DEVICES	China	202110772499.8	Jul 8, 2021	CN113921397A	Jan 11, 2022			Published	Subhash Srinivas Pidaparthi, Andrew P. Edwards, Clifford Drowley, Kedar Patel
147	102584-1254457	007810CN	SELF-ALIGNED ISOLATION FOR SELF-ALIGNED CONTACTS FOR VERTICAL FETS	China	202110801885.5	Jul 15, 2021	CN113948393A	Jan 18, 2022			Published	Clifford Drowley, Hao Cui, Andrew P. Edwards, Subhash Srinivas Pidaparthi
148	102584-1269227	007910CN	NONUNIFAR, DISCRETE TIME CONTROL OF POWER FACTOR CORRECTION POWER CONVERTER	China	2021113566760	Nov 16, 2021	CN 114515120 A	May 17, 2022			Published	Anders Lind
149	102584-1282718	007920CN	METHOD AND SYSTEM FOR CONTROLLING THE POWER FACTOR OF A POWER CONVERTER	China	2021113579972	Nov 16, 2021	CN 114513121 A	May 17, 2022			Published	Anders Lind
150	102584-1269336	008010CN	METHOD AND SYSTEM FOR ENTERING AND EXITING A FREQUENCY CLAMP MODE FOR VARIABLE FREQUENCY, OFFLINE SWITCH-MODE POWER CONVERTERS	China	202111358017.0	Nov 16, 2021	CN 114513113 A	May 17, 2022			Published	Anders Lind
151	102584-1269228	008110CN	SELF-OSCILLATING HIGH FREQUENCY CONVERTER WITH POWER FACTOR CORRECTION	China	202111200072.7	Oct 14, 2021	CN114362546A	Apr 15, 2022			Published	Charles Coles
152	102584-1269340	008210CN	METHOD AND APPARATUS FOR DIGITAL, CLOSED-LOOP CONTROL OF CRCM SWITCH-MODE POWER CONVERTERS	China	202111356379.6	Nov 16, 2021	CN114513119A	May 17, 2022			Published	Anders Lind
153	102584-1282398	008220CN	METHOD AND APPARATUS FOR OVER-CURRENT PROTECTION AND CRCM CONTROL IN POWER CONVERTERS	China	202111357601.4	Nov 16, 2021	CN 114513115 A	May 17, 2022			Published	Anders Lind
154	102584-1282492	008230CN	METHOD AND APPARATUS FOR SENSING THE INPUT VOLTAGE OF A POWER CONVERTER	China	202111356357.X	Nov 16, 2021	CN114578123A	Jun 3, 2022			Published	Anders Lind
155	102584-1300016	008310CN	METHODS AND SYSTEMS FOR FABRICATION OF VERTICAL FIN-BASED JFETS	China	2022101227924	Feb 9, 2022	CN 114914303 A	Aug 16, 2022			Published	Clifford Drowley, Hao Cui, Andrew P. Edwards, Subhash Srinivas Pidaparthi
156	102584-1295503	008410CN	COUPLED GUARD RINGS FOR EDGE TERMINATION	China	2022101070947	Jan 28, 2022	CN114823846A	Jul 29, 2022			Published	Clifford Drowley, Andrew P. Edwards, Hao Cui, Subhash Srinivas Pidaparthi
157	102584-1300017	008510CN	METHOD AND SYSTEM FOR CONTROL OF SIDEWALL ORIENTATION IN VERTICAL GALLIUM NITRIDE FIELD EFFECT TRANSISTORS	China	2022103644503	Apr 7, 2022	CN 115207123 A	Oct 18, 2022			Published	Clifford Drowley, Andrew P. Edwards, Hao Cui, Subhash Srinivas Pidaparthi, Michael Craven, David DeMuyne
158	102584-1300018	008610CN	METHOD AND SYSTEM TO IMPROVE UNIFORMITY IN POWER FET ARRAYS	China	2022103644594	Apr 7, 2022	CN 115207124 A	Oct 18, 2022			Published	Clifford Drowley, Andrew P. Edwards, Hao Cui, Subhash Srinivas Pidaparthi
159	102584-1372839	008710CN	VERTICAL FIN-BASED FIELD EFFECT TRANSISTOR (FINFET) WITH VARYING CONDUCTIVITY REGIONS	China	2023101182858	Feb 15, 2023	CN 116613163 A	Aug 18, 2023			Published	Clifford Drowley, Andrew J. Walker, Andrew P. Edwards, Subhash Srinivas Pidaparthi
160	102584-1380933	008810CN	NEGATIVE CHARGE EXTRACTION STRUCTURE FOR EDGE TERMINATION	China	2023104726308	Apr 27, 2023	CN 116978926 A	Oct 31, 2023			Published	Kyoung Wook Seok, Clifford Drowley, Andrew J. Walker, Andrew P. Edwards
161	102584-1362418	008910CN	A VERTICAL FIN-BASED FIELD EFFECT TRANSISTOR (FINFET) WITH NEUTRALIZED FIN TIPS	China	2023100427928	Jan 28, 2023	CN 116525675 A	Aug 1, 2023			Published	Subhash Srinivas Pidaparthi, Clifford Drowley, Shahin Sharifzadeh, Andrew P. Edwards, Andrew Walker, Francis Chai
162	102584-1363545	009010CN	METHOD AND SYSTEM FOR FABRICATING REGROWN FIDUCIALS FOR SEMICONDUCTOR DEVICES	China	2023100570470	Jan 17, 2023	CN 116469821 A	Jul 21, 2023			Published	Karthik Suresh Anulalan, Jianfeng Wang, Sharlene Wilson, Mark Curtice, Subhash Srinivas Pidaparthi, Clifford Drowley
163	102584-1380937	009210CN	METHOD AND SYSTEM FOR FIN-BASED VOLTAGE CLAMP	China	2023104642139	Apr 26, 2023	CN116954293A	Oct 27, 2023			Published	Andrew J. Walker, Clifford Drowley, Subhash Srinivas Pidaparthi, Andrew P. Edwards, Shahin Sharifzadeh, Joseph Tandinjan
164	102584-1380940	009310CN	VERTICAL FIN-BASED FIELD EFFECT TRANSISTOR (FINFET) WITH CONNECTED FIN TIPS	China	2023104284285	Apr 20, 2023	CN 116913918 A	Oct 20, 2023			Published	Andrew P. Edwards, Andrew J. Walker, Clifford Drowley, Subhash Srinivas Pidaparthi
165	102584-1380942	009410CN	METHOD AND SYSTEM FOR ROUTING OF ELECTRICAL CONDUCTORS OVER NEUTRALIZED POWER FETS	China	2023104285324	Apr 20, 2023	CN 116913919 A	Oct 20, 2023			Published	Clifford Drowley, Andrew J. Walker, Andrew P. Edwards, Subhash Srinivas Pidaparthi, Thomas E. Kopley

SCHEDULE B

Trademarks

Trademarks:

- NEXGEN VERTICAL GAN
- NEXGEN HELIOS
- MERLIN POWER ENGINE

Domain Names:

- nexgenpowersystems.com
- nxgpower.systems
- nxgpower.co
- nxgpower.net
- nxgpower.com